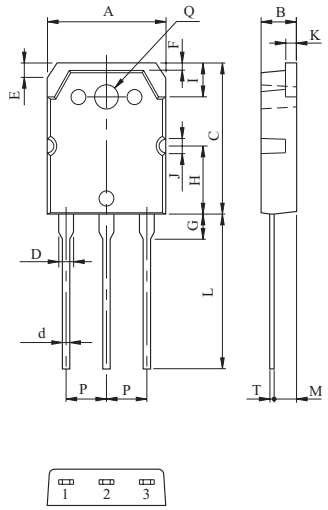
TIP35C

TRIPLE DIFFUSED NPN TRANSISTOR

HIGH POWER AMPLIFIER APPLICATION.

FEATURES

- Recommended for 75W Audio Frequency Amplifier Output Stage.
- Complementary to TIP36C.
- Icmax:25A.



DIM	MILLIMETERS
A	15.9 MAX
B	4.8 MAX
C	20.0±0.3
D	2.0±0.3
d	1.0+0.3/-0.25
E	2.0
F	1.0
G	3.3 MAX
H	9.0
I	4.5
J	2.0
K	1.8 MAX
L	20.5±0.5
M	2.8
P	5.45±0.2
Q	Φ3.2±0.2
T	0.6+0.3/-0.1

TO-3P(N)

MAXIMUM RATING (Ta=25℃)

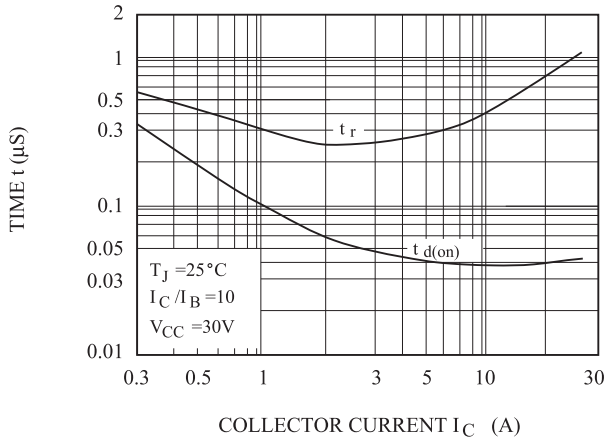
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V_{CEO}	100	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	25	A
Base Current	I_B	5.0	A
Collector Power Dissipation (Tc=25℃)	P_C	125	W
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55～150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

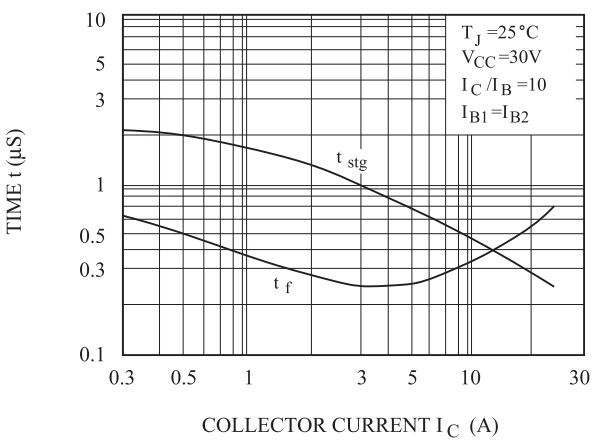
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=100V, I_E=0	-	-	10	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=5V, I_C=0	-	-	10	μA
Collector-emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=50mA, I_B=0	100	-	-	V
DC Current Gain	h_{FE}(1) (Note)	V_{CE}=5V, I_C=1.5A	55	-	160	
	h_{FE}(2)	V_{CE}=4V, I_C=15A	15	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$(1)	I_C=15A, I_B=1.5A	-	-	1.8	V
	$V_{CE(sat)}$(2)	I_C=25A, I_B=5.0A	-	-	4.0	
Base-Emitter Voltage	V_{BE}	V_{CE}=5V, I_C=5A	-	-	1.5	V
Transition Frequency	f_T	V_{CE}=5V, I_C=1A	3.0	-	-	MHz

Note : h_{FE}(1) Classification R:55~110, O:80~160

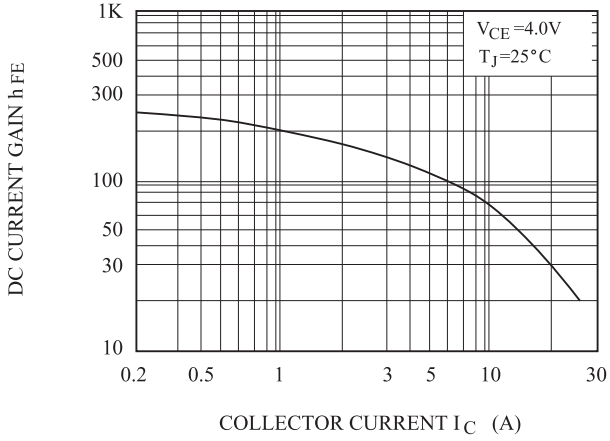
SWITCHING CHARACTERISTICS



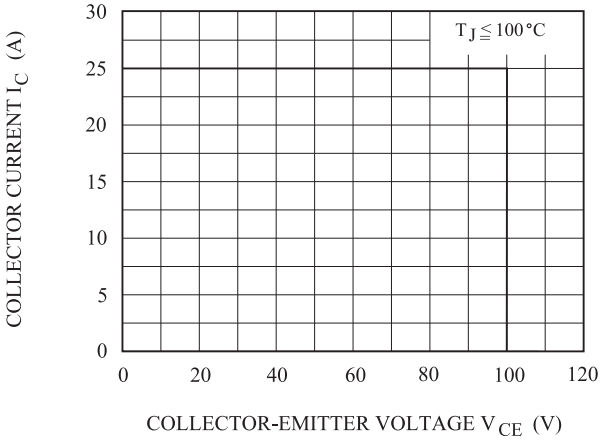
SWITCHING CHARACTERISTICS



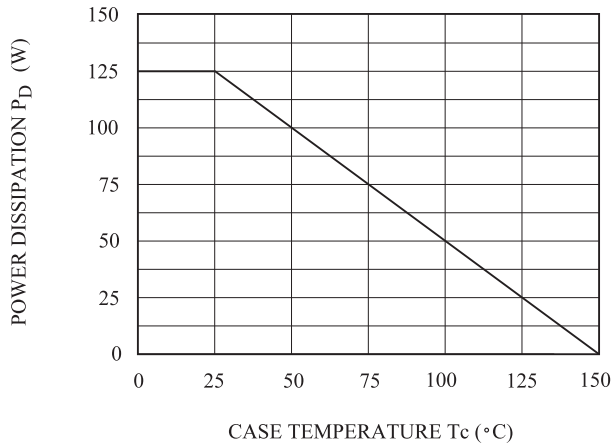
h FE - I C



REVERSE BIAS SAFE OPERATING AREA



P D - Tc



FORWARD BIAS SAFE OPERATING AREA

